
2SJ351, 2SJ352

Silicon P-Channel MOS FET

HITACHI

ADE-208-143
1st. Edition

Application

Low frequency power amplifier

Complementary pair with 2SK2220, 2SK2221

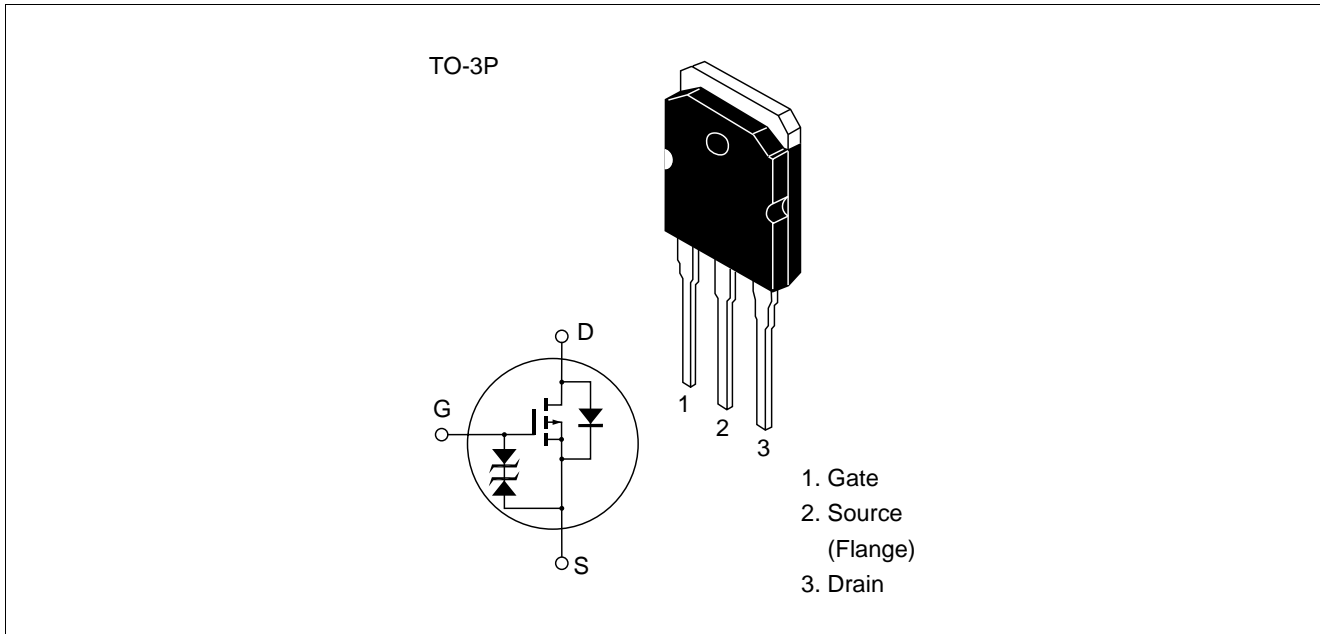
Features

- High power gain
- Excellent frequency response
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes

Ordering Information

Type No.	V_{DSX}
2SJ351	-180 V
2SJ352	-200 V

Outline



Absolute Maximum Ratings (Ta = 25°C)

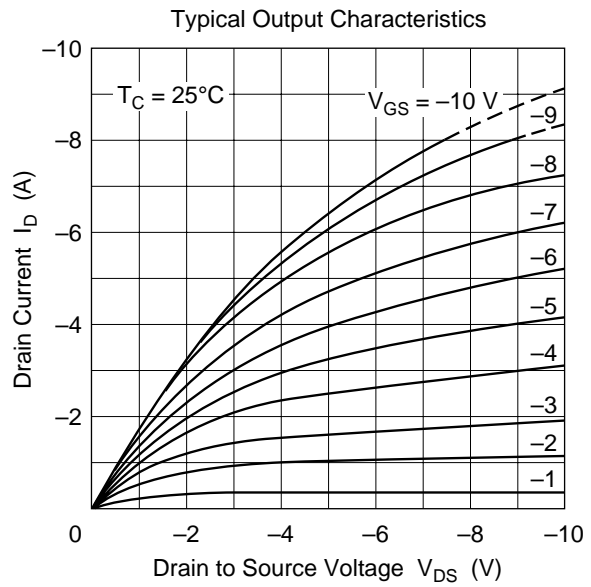
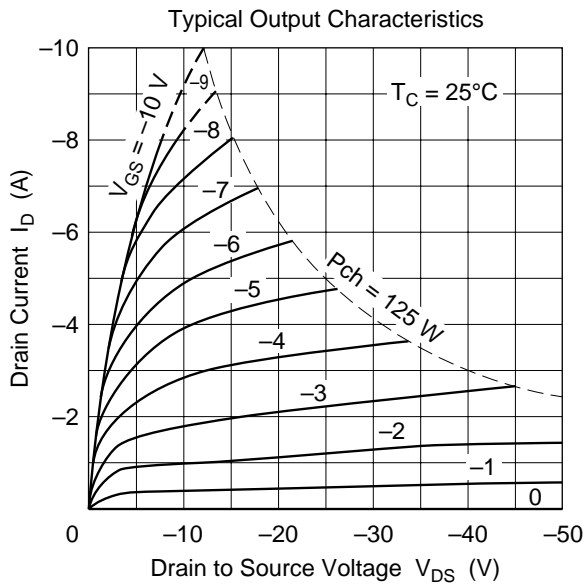
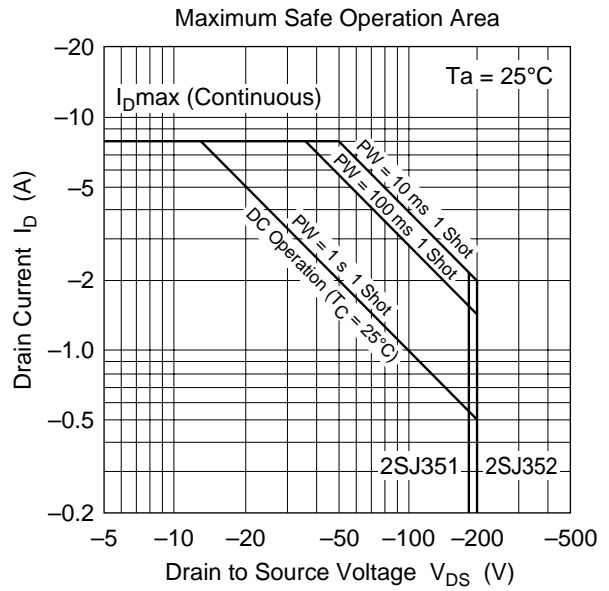
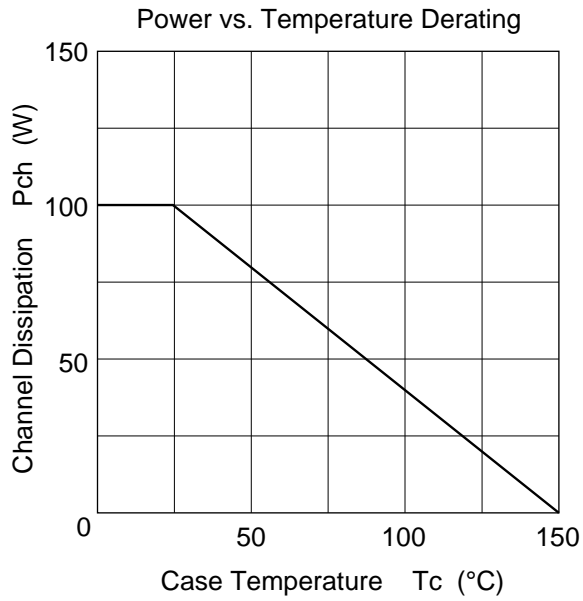
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ351	V_{DSX}	-180	V
	2SJ352		-200	
Gate to source voltage		V_{GSS}	±20	V
Drain current		I_D	-8	A
Body to drain diode reverse drain current		I_{DR}	-8	A
Channel dissipation		P_{ch}^{*1}	100	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C

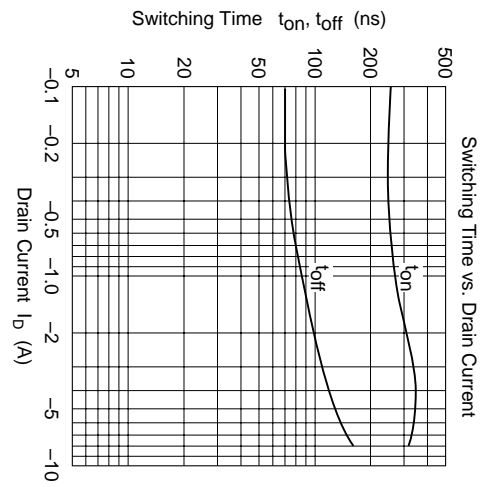
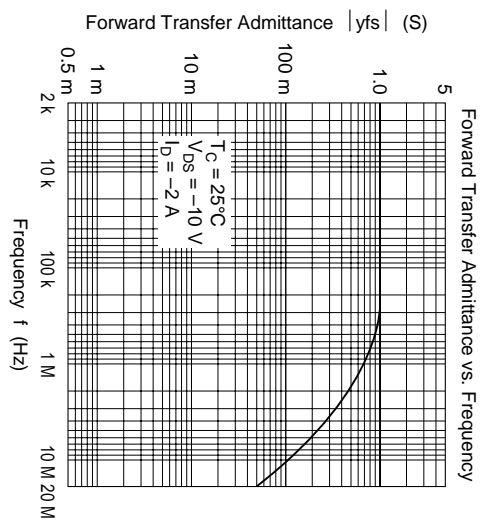
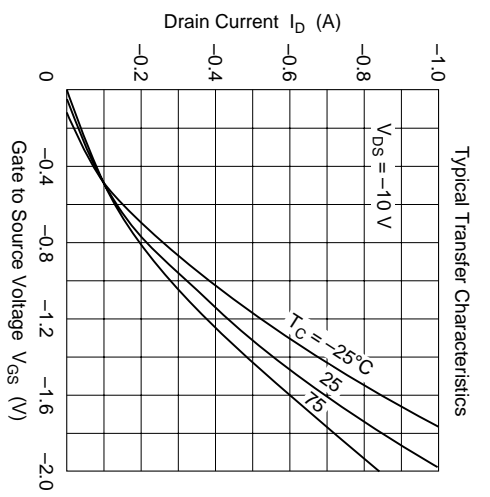
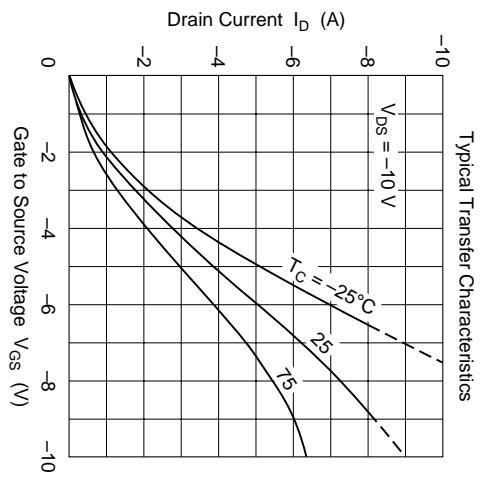
Note: 1. Value at $T_c = 25^\circ\text{C}$

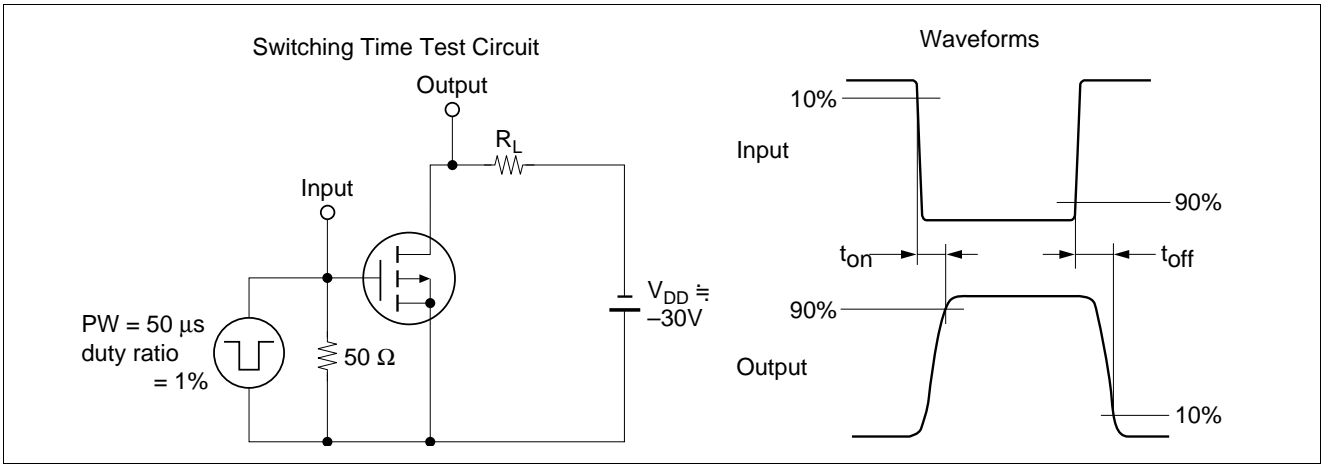
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ351 $V_{(BR)DSX}$	-180	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 10 \text{ V}$
	2SJ352	-200	—	—		
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.15	—	-1.45	V	$I_D = -100 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Drain to source saturation voltage	$V_{DS(sat)}$	—	—	-12	V	$I_D = -8 \text{ A}$, $V_{GD} = 0^{*1}$
Forward transfer admittance	$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	Ciss	—	800	—	pF	$V_{GS} = 5 \text{ V}$, $V_{DS} = -10 \text{ V}$,
Output capacitance	Coss	—	1000	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	Crss	—	18	—	pF	
Turn-on time	t_{on}	—	320	—	ns	$V_{DD} = -30 \text{ V}$, $I_D = -4 \text{ A}$
Turn-off time	t_{off}	—	120	—	ns	

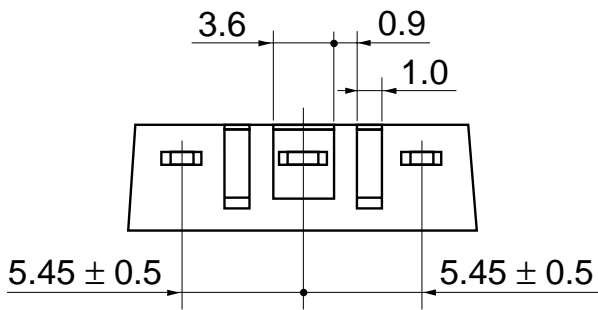
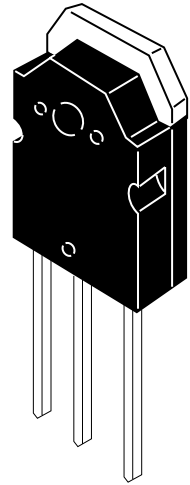
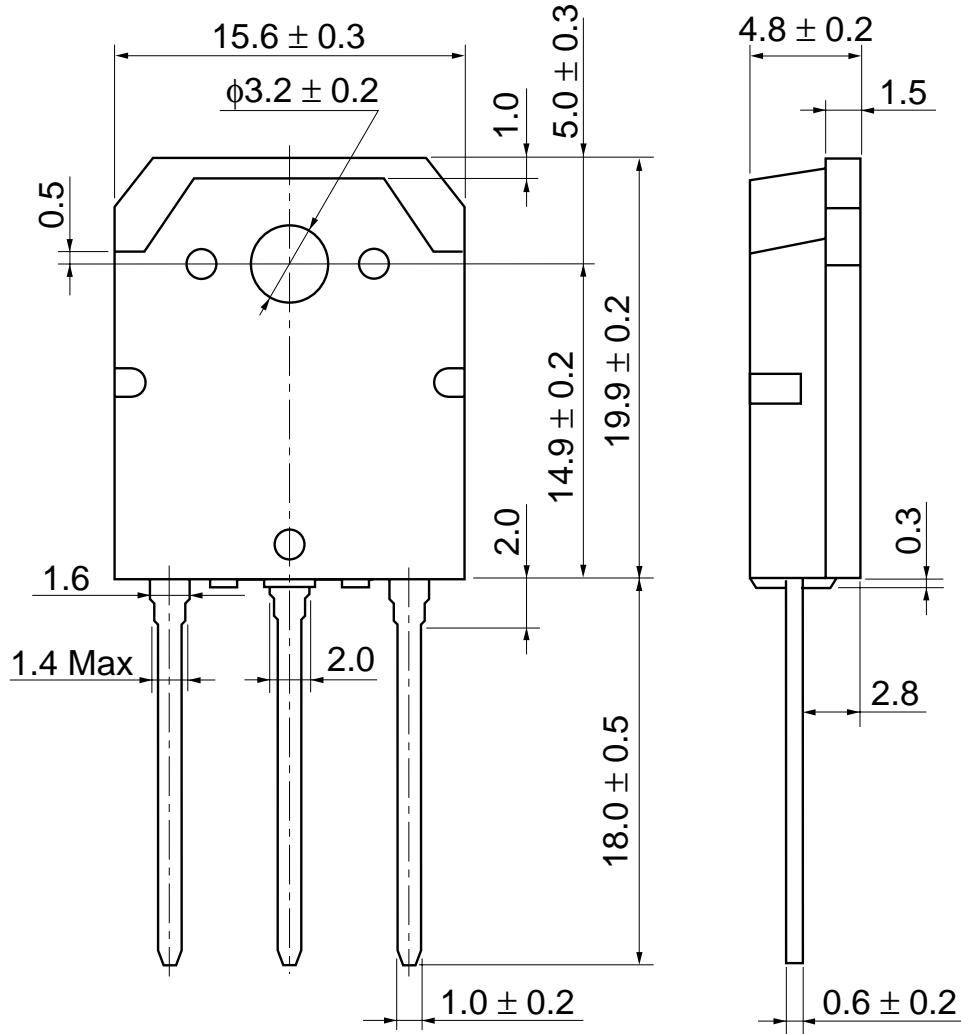
Note: 1. Pulse test







Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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